

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Withdrawn) A method for manufacturing a semiconductor device comprising the steps of:

performing a heating process on a first semiconductor film to form a second semiconductor film;

irradiating laser light to the second semiconductor film to form a third semiconductor film having a plurality of convexes; and

irradiating intense light to the third semiconductor film to form a fourth semiconductor film.

2. (Withdrawn) A method for manufacturing a semiconductor device according to claim 1, wherein the intense light is irradiated from above the substrate, from below the substrate or from above and below the substrate.

3. (Withdrawn) A method for manufacturing a semiconductor device according to claim 1, wherein the intense light is selected from the group consisting of infrared light, visible light and ultraviolet light.

4. (Withdrawn) A method for manufacturing a semiconductor device according to claim 1, wherein the intense light is light emitted from a lamp selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high-pressure sodium lamp or a high-pressure mercury lamp.

5. (Withdrawn) A method for manufacturing a semiconductor device according to claim 1, wherein an atmosphere within a process chamber when irradiating the intense light is a reducing gas.

6. (Withdrawn) A method for manufacturing a semiconductor device according to claim 1, wherein the laser light is emitted from a laser selected from the group consisting of an excimer laser, a YAG laser, a YVO<sub>4</sub> laser, a YAlO<sub>3</sub> laser and a YLF laser.

7. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

irradiating a first intense light to a first semiconductor film to form a second semiconductor film;

irradiating laser light to the second semiconductor film to form a third semiconductor film having a plurality of convexes; and

irradiating a second intense light directly to the third semiconductor film to form a fourth semiconductor film.

8. (Currently Amended) A method for manufacturing a semiconductor device according to claim 7, wherein the first and second intense ~~light is~~ lights are irradiated from above ~~the~~ a substrate on which the first semiconductor film is formed, from below ~~the~~ said substrate or from above and below ~~the~~ said substrate.

9. (Currently Amended) A method for manufacturing a semiconductor device according to claim 7, wherein the first and second intense ~~light is~~ lights are selected from the group consisting of infrared light, visible light and ultraviolet light.

10. (Currently Amended) A method for manufacturing a semiconductor device according to claim 7, wherein the first and second intense light ~~is~~ lights are light emitted from a lamp selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high-pressure sodium lamp or a high-pressure mercury lamp.

11. (Currently Amended) A method for manufacturing a semiconductor device according to claim 7, wherein an atmosphere within a process chamber when irradiating the first and second intense light lights is ~~a reducing gas~~ selected from nitrogen gas and an inert gas.

12. (Currently Amended) A method for manufacturing a semiconductor device according to claim 7, wherein the laser light is emitted from a laser selected from the group consisting of an excimer laser, a YAG laser, a YVO<sub>4</sub> laser, a YAlO<sub>3</sub> laser and a YLF laser.

13. (Withdrawn) A method for manufacturing a semiconductor device comprising the steps of:

providing a first semiconductor film with a metal element for promoting crystallization;

performing a heating process on a first semiconductor film to form a second semiconductor film;

irradiating laser light to the second semiconductor film to form a third semiconductor film having a plurality of convexes; and

irradiating intense light to the third semiconductor film to form a fourth semiconductor film.

14. (Withdrawn) A method for manufacturing a semiconductor device according to claim 13, wherein the intense light is irradiated from above the substrate, from below the substrate or from above and below the substrate.

15. (Withdrawn) A method for manufacturing a semiconductor device according to claim 13, wherein the intense light is selected from the group consisting of infrared light, visible light and ultraviolet light.

16. (Withdrawn) A method for manufacturing a semiconductor device according to claim 13, wherein the intense light is light emitted from a lamp selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high-pressure sodium lamp or a high-pressure mercury lamp.

17. (Withdrawn) A method for manufacturing a semiconductor device according to claim 13, wherein an atmosphere within a process chamber when irradiating the intense light is a reducing gas.

18. (Withdrawn) A method for manufacturing a semiconductor device according to claim 13, wherein the laser light is emitted from a laser selected from the group consisting of an excimer laser, a YAG laser, a YVO<sub>4</sub> laser, a YAlO<sub>3</sub> laser and a YLF laser.

19. (Withdrawn) A method for manufacturing a semiconductor device according to claim 13, wherein the metal element is one or a plurality of elements selected from Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Sn and Sb.

20. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

providing a first semiconductor film with a metal for promoting crystallization;  
irradiating a first intense light to the first semiconductor film to form a second semiconductor film;  
irradiating laser light to the second semiconductor film to form a third semiconductor film having a plurality of convexes; and  
irradiating a second intense light directly to the third semiconductor film to form a fourth semiconductor film.

21. (Currently Amended) A method for manufacturing a semiconductor device according to claim 20, wherein the first and second intense ~~light is~~ lights are irradiated from above the a substrate on which the first semiconductor film is formed, from below the said substrate or from above and below the said substrate.

22. (Currently Amended) A method for manufacturing a semiconductor device according to claim 20, wherein the first and second intense ~~light is~~ lights are selected from the group consisting of infrared light, visible light and ultraviolet light.

23. (Currently Amended) A method for manufacturing a semiconductor device according to claim 20, wherein the first and second intense ~~light is~~ lights are emitted from a lamp selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high-pressure sodium lamp and a high-pressure mercury lamp.

24. (Currently Amended) A method for manufacturing a semiconductor device according to claim 20, wherein an atmosphere within a process chamber when irradiating the first and second intense ~~light~~ lights is ~~a reducing gas~~ selected from nitrogen gas and an inert gas.

25. (Original) A method for manufacturing a semiconductor device according to claim 20, wherein the laser light is emitted from a laser selected from the group consisting of an excimer laser, a YAG laser, a YVO<sub>4</sub> laser, a YAlO<sub>3</sub> laser and a YLF laser.

26. (Original) A method for manufacturing a semiconductor device according to claim 20, wherein the metal element is one or a plurality of elements selected from Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Sn and Sb.

27. (Currently Amended) A method of manufacturing a semiconductor device comprising:

- providing a semiconductor film with a metal for promoting crystallization;
- crystallizing said semiconductor film;
- irradiating the crystallized semiconductor film with laser light to increase a crystallinity of the crystallized semiconductor film;
- irradiating intense light directly to the crystallized semiconductor film after the irradiation of the laser light.

28. (New) A method for manufacturing a semiconductor device according to claim 27, wherein the intense light is irradiated from above a substrate on which the first semiconductor film is formed, from below said substrate or from above and below said substrate.

29. (New) A method for manufacturing a semiconductor device according to claim 27, wherein the intense light is selected from the group consisting of infrared light, visible light and ultraviolet light.

30. (New) A method for manufacturing a semiconductor device according to claim 27, wherein the intense light is emitted from a lamp selected from the group consisting of a halogen lamp, a metal halide lamp, a xenon arc lamp, a carbon arc lamp, a high-pressure sodium lamp and a high-pressure mercury lamp.

31. (New) A method for manufacturing a semiconductor device according to claim 27, wherein an atmosphere within a process chamber when irradiating the intense light is selected from nitrogen gas and an inert gas.

32. (New) A method for manufacturing a semiconductor device according to claim 27, wherein the laser light is emitted from a laser selected from the group consisting of an excimer laser, a YAG laser, a YVO<sub>4</sub> laser, a YAlO<sub>3</sub> laser and a YLF laser.

33. (New) A method for manufacturing a semiconductor device according to claim 20, wherein the metal element is one or a plurality of elements selected from Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Sn and Sb.